

Silicon PNP transistor epitaxial type B5850

[Applications]

General purpose transistors
Medium power amplifier and switching

[Feature]

High break-down voltage $BVCEO = -80V$
Low collector saturation voltage $VCE(sat) = -0.14V$ (Typ.) at $IC = -500mA$, $IB = -50mA$
Small output capacitance $C_{ob} = 8pF$ (Typ.) at $VCB = -10V$, $f = 1MHz$
Complementary pair with D5850

[Absolute maximum ratings (Ta=25C)]

Characteristic	Symbol	Maximum ratings	Unit
Collector-base voltage	$VCBO$	-80	V
Collector-emitter voltage	$VCEO$	-80	V
Emitter-base voltage	$VEBO$	-8	V
Collector current	IC	-1000	mA
Junction temperature	T_j	150	C
Storage temperature	T_{stg}	-55 to 150	C

[Electrical characteristics (Ta=25C)]

Characteristic	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BVCBO$	-80	-	-	V	$IC = -50\mu A$, $IE = 0A$
Collector-emitter breakdown voltage	$BVCEO$	-80	-	-	V	$IC = -2mA$, $IB = 0A$
Emitter-base breakdown voltage	$BVEBO$	-8	-	-	V	$IE = -50\mu A$, $IC = 0A$
Collector cut-off current	$ICBO$	-	-	-0.5	μA	$VCB = -50V$, $IE = 0A$
Emitter cut-off current	$IEBO$	-	-	-0.5	μA	$VEB = -8V$, $IE = 0A$
DC current gain	hFE	56	-	390	-	$VCE = -10V$, $IC = -150mA$
Collector-emitter saturation voltage	$VCE(sat)$	-	-0.14	-0.4	V	$IC = -500mA$, $IB = -50mA$
Transition frequency	f_T	-	180	-	MHz	$VCE = -10V$, $IE = 50mA$
Collector output capacitance	C_{ob}	-	8	20	pF	$VCB = -10V$, $f = 1MHz$, $IE = 0A$

Notice 1) These are measured data of transistors assembled by PHENITEC SEMICONDUCTOR Corp. and are for reference only.

Notice 2) The contents described herein are subject to change without notice.

No. B5850-20160808

